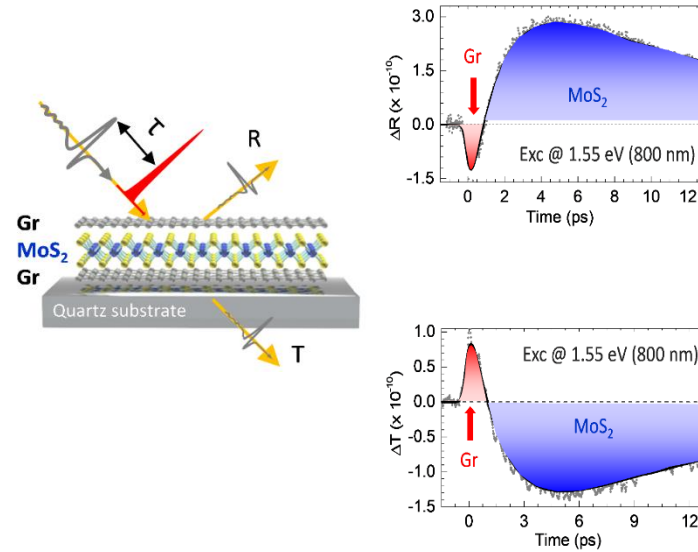


THz conductivity and photo-induced carrier dynamics in a Graphene/MoS₂/Graphene heterostructure



S. Kumar, A. Singh, A. Nivedan, S. Kumar

Department of Physics, Indian Institute of Technology Delhi, New Delhi 110016, India

S. J. Yun, Y. H. Lee

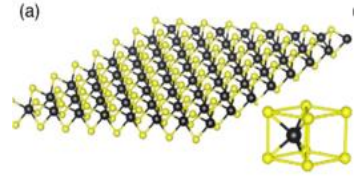
Department of Energy Science, Sungkyunkwan University (SKKU), Suwon 16419, Republic of Korea

M. Tondusson, J. Degert, J. Oberle, E. Freysz

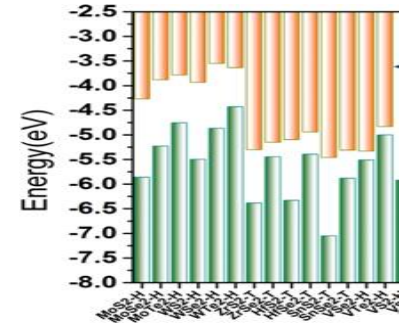
Univ. Bordeaux, CNRS, LOMA UMR 5798, 33405 Talence, France

Introduction

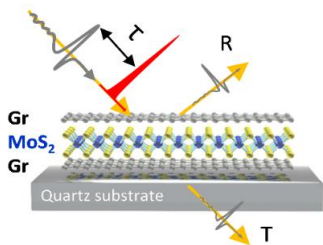
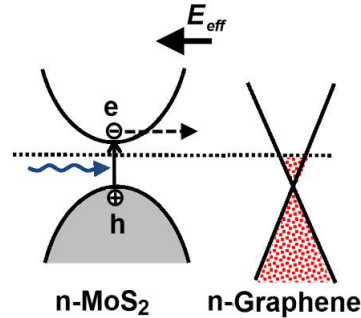
Single layer of transition metal dichalcogenite (TMDC) such as MoS_2 , WS_2 , MoSe_2 , are 2D materials which offer many prospects in optoelectronics, optics, etc...



Heterostructures of semiconducting TMDC's can be easily prepared to further extend the range of applications of these materials and give rise to new type of excitons where e^- and hole are localized in different layers of TMDC.

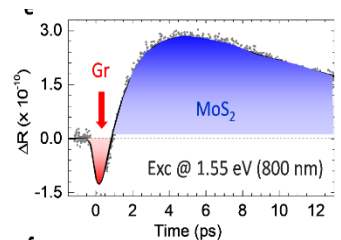


Heterostructure of TMDC with graphene have also been prepared and studied. It has been shown that when excited above the band gap of the TMDC the e^- are rapidly transferred from TMDC to graphene.



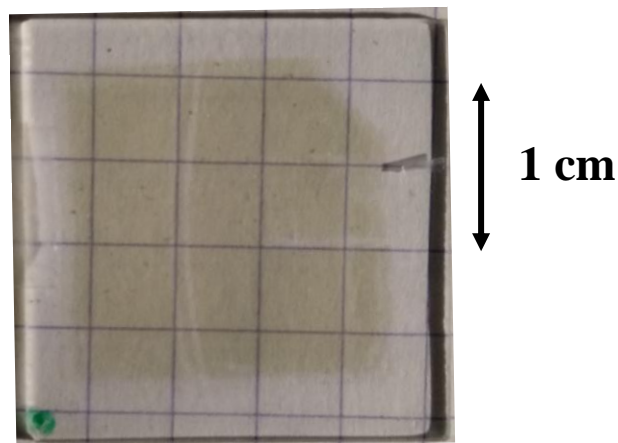
We have prepared a **Graphene/MoS₂/Graphene** heterostructure. Using optical absorption, Raman spectroscopy and TDS-THz spectroscopy we characterized the properties of this heterostructure.

Time resolved optical-pump THz-probe experiment indicates that below the band gap of MoS₂ carriers generated in graphene can be transiently transferred in MoS₂



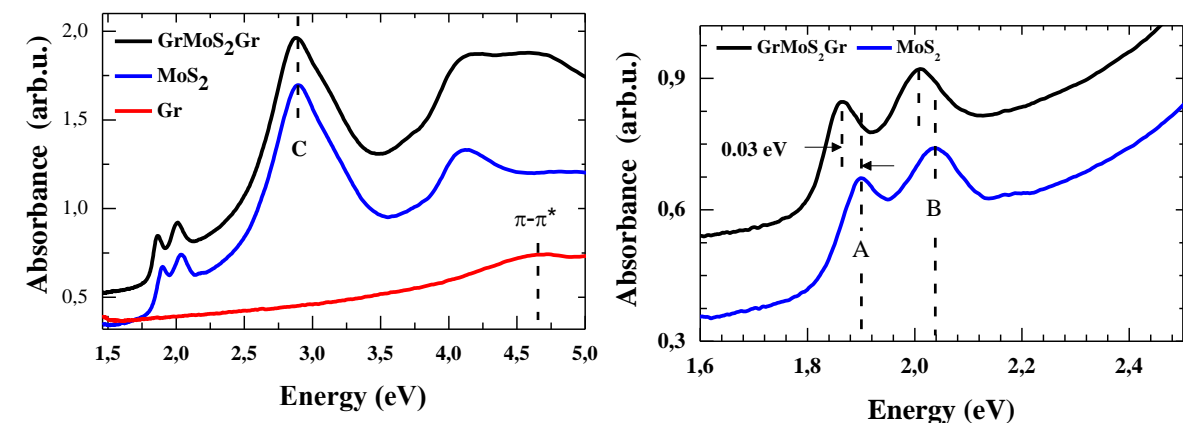
Studied sample and their characterisations.

Large CVD grown samples of Graphene (Gr), MoS₂ and Gr/MoS₂/Gr transferred on quartz

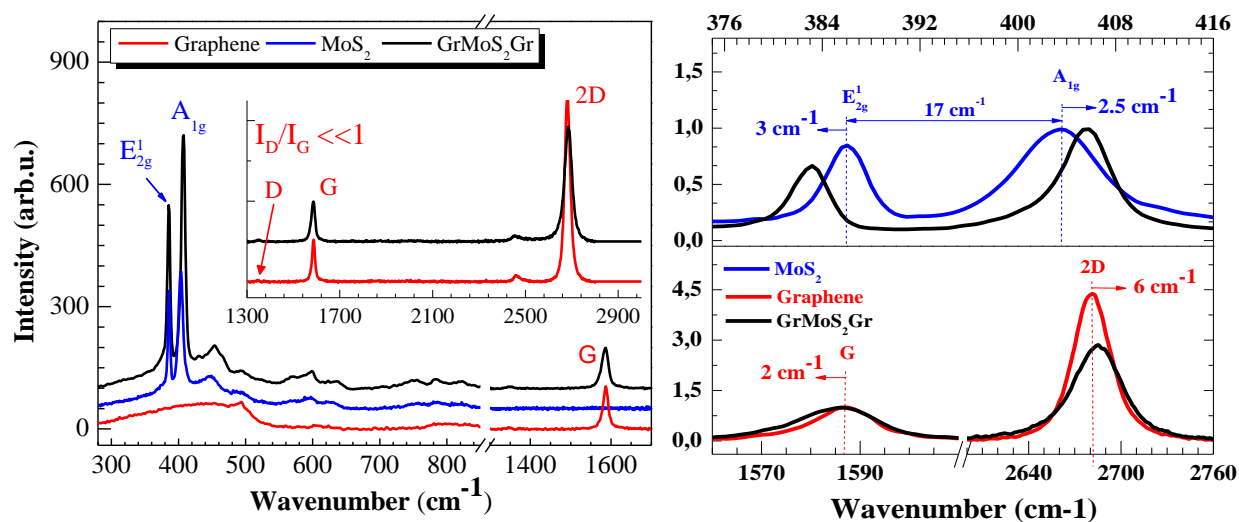


Absorption spectra in visible and U.V. range

Raman spectra

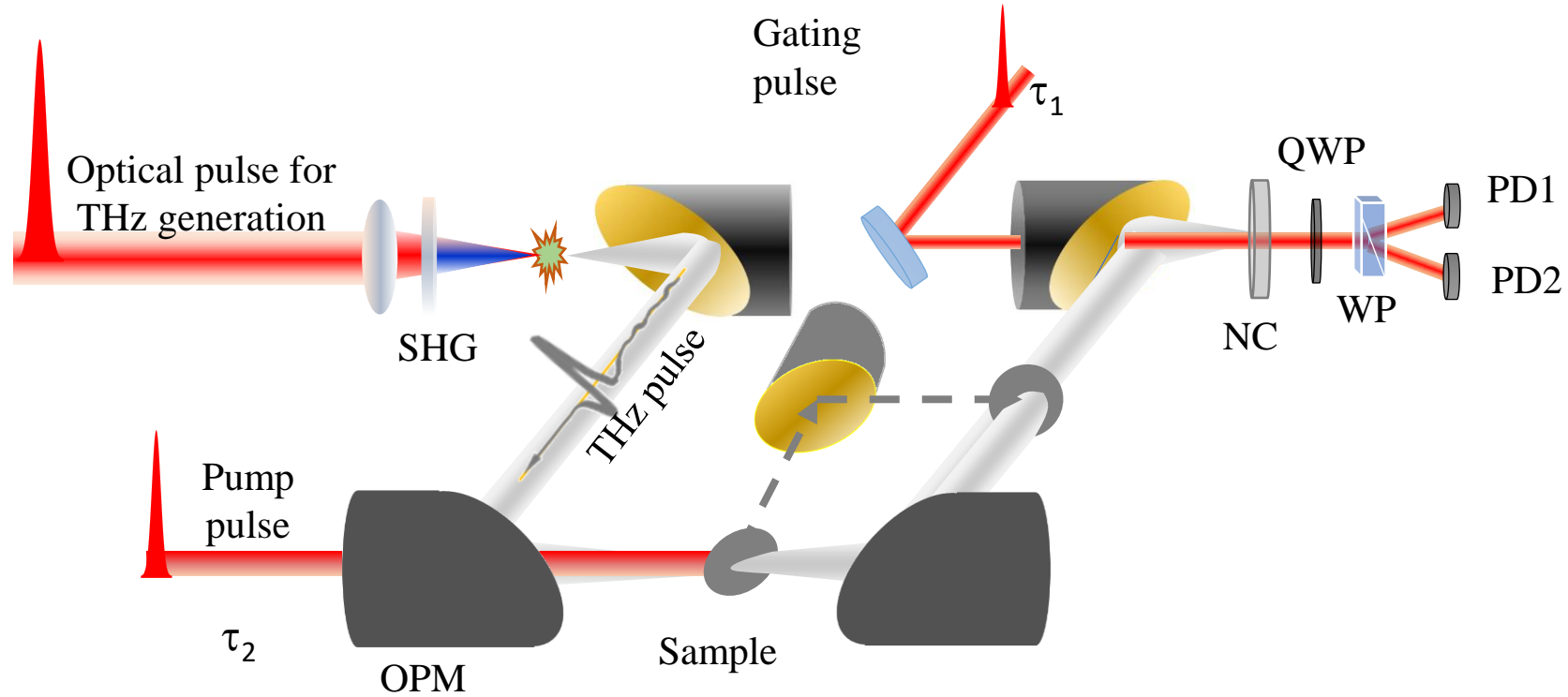


A, B and C exciton at ~1.86 eV, ~2.01 eV and 2.70 eV in MoS₂
Band Gap in MoS₂ ~1.90 eV

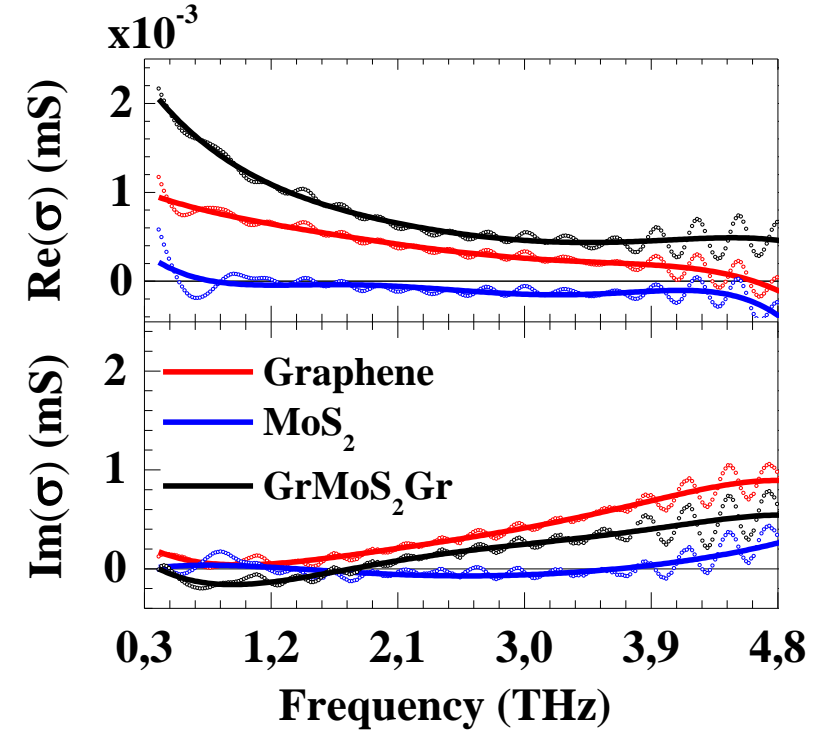
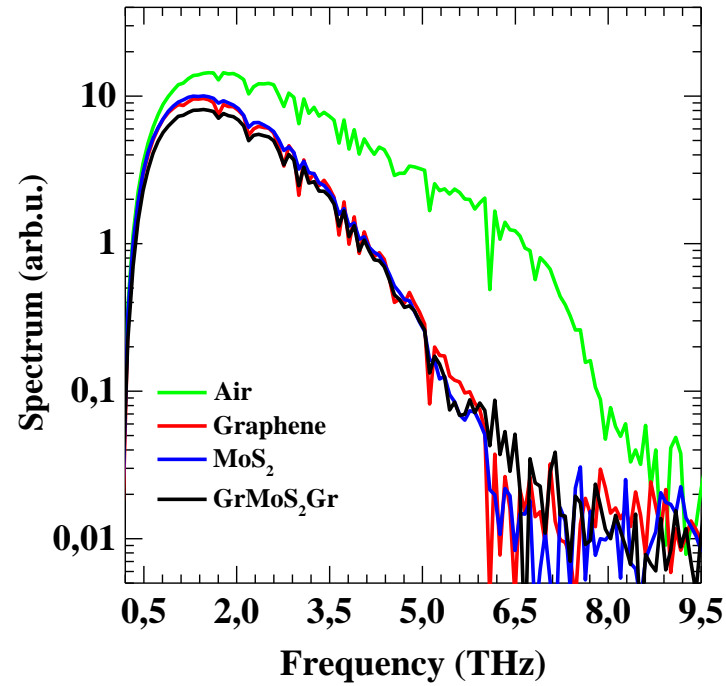
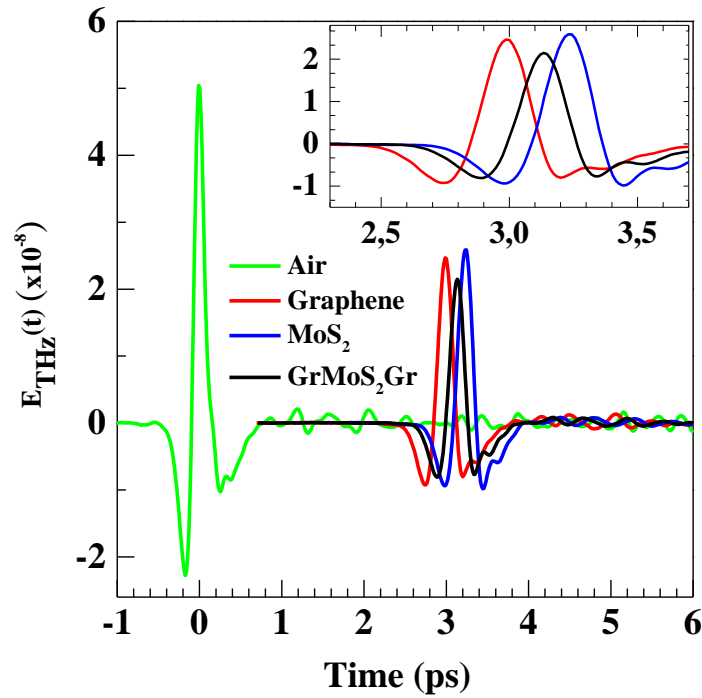


In Graphene $I_{2D}/I_G = 2$ and I_D mode characterizes the defects

THz-TDS spectroscopy and Optical pump – THz probe set-up



THz -TDS of the studied samples



Optical pump – THz probe on Graphene and MoS₂

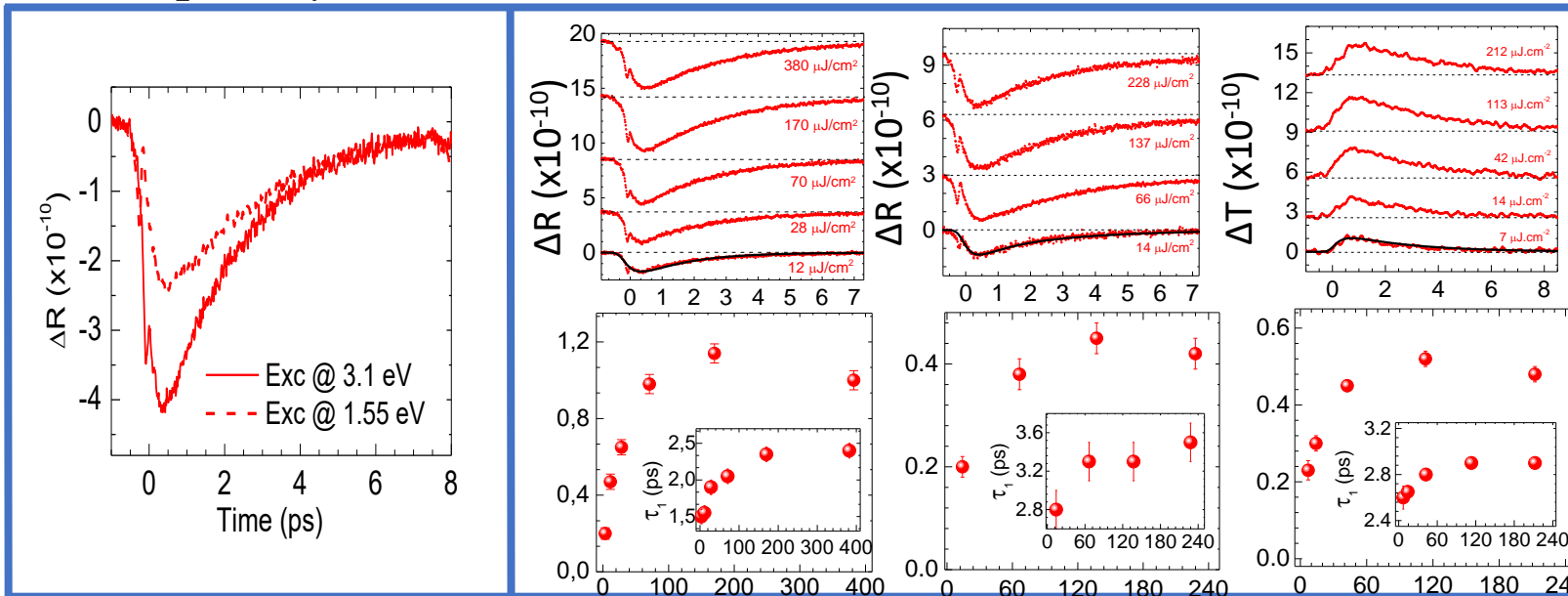
Pump = 20 $\mu\text{J} \cdot \text{cm}^{-2}$

Exc. @ 3.1 eV (400 nm)

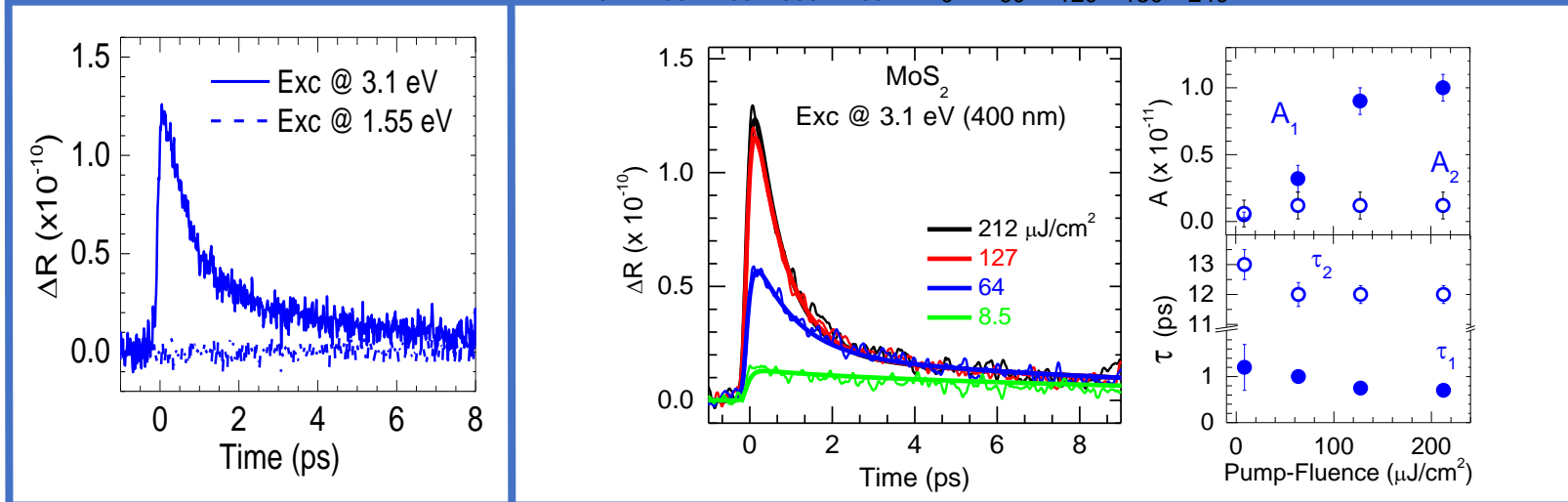
Exc. @ 1.55 eV (800 nm)

Exc. @ 1.55 eV (800 nm)

Graphene



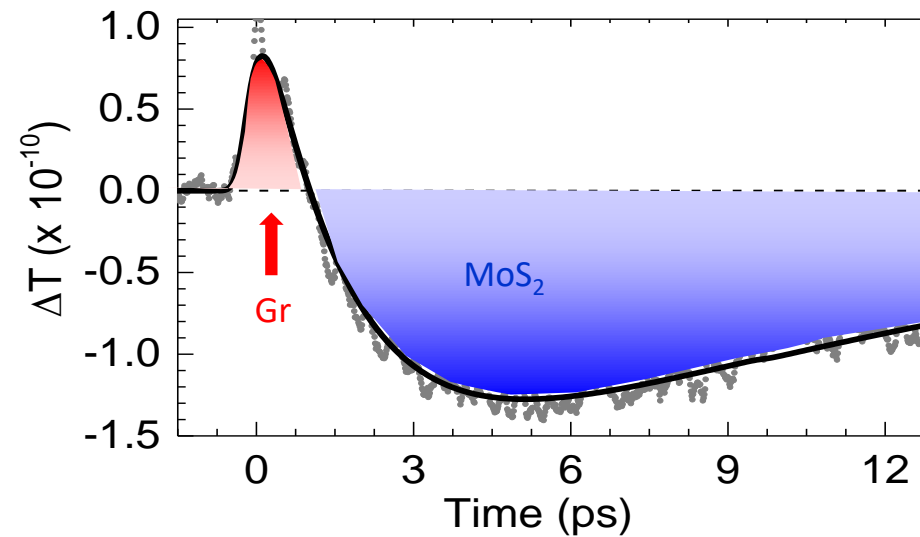
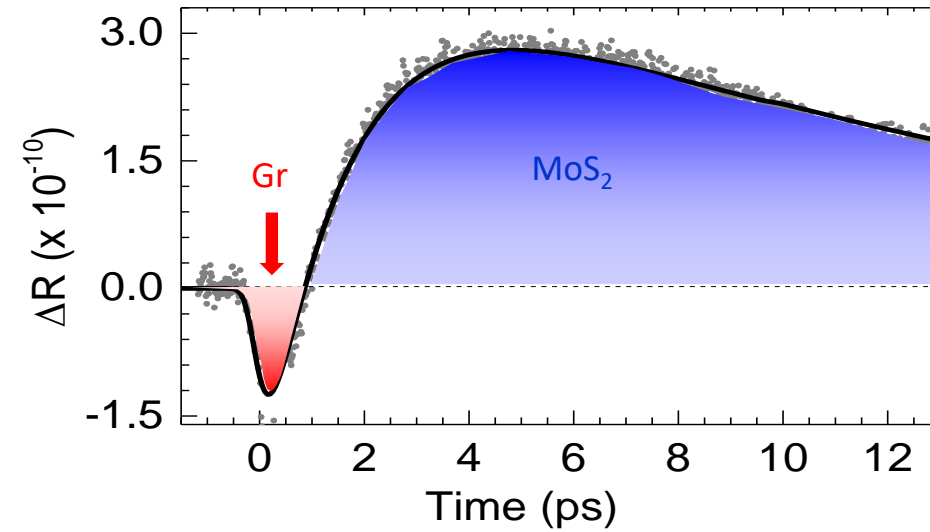
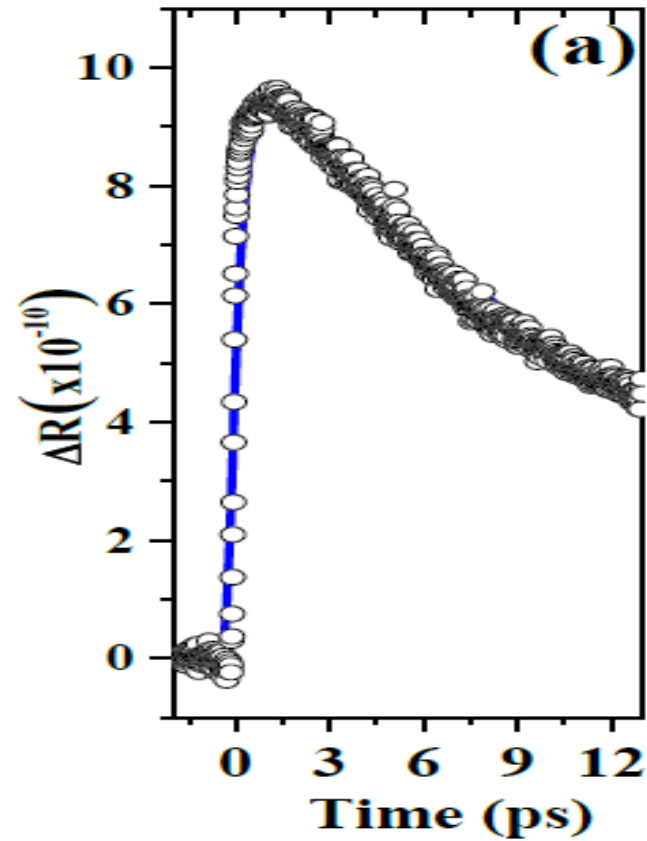
MoS₂



Optical pump – THz probe on GrMoS₂Gr

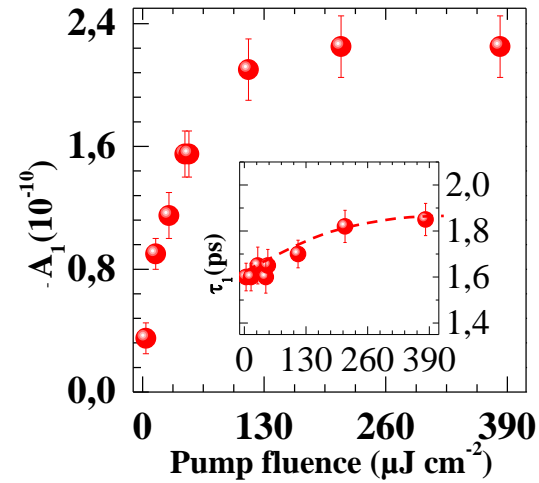
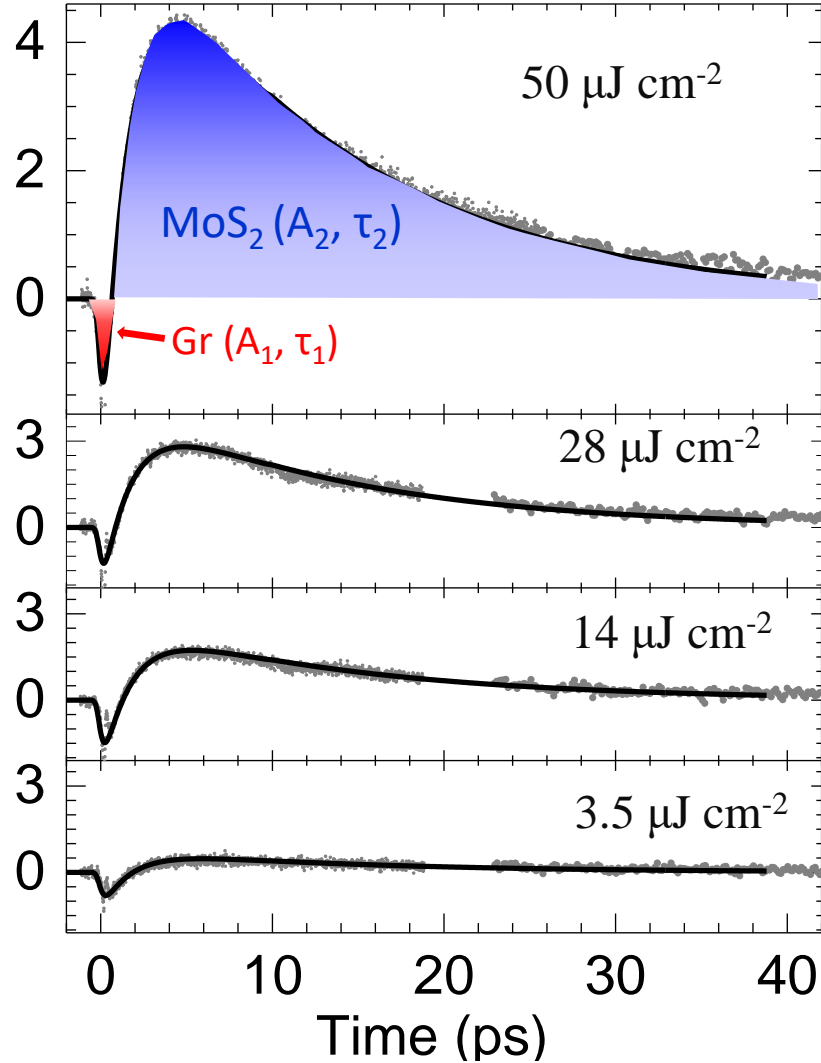
Exc @ 1.55 eV (800 nm)

$\lambda_p = 3.1 \text{ eV} (0.4 \text{ } \mu\text{m})$

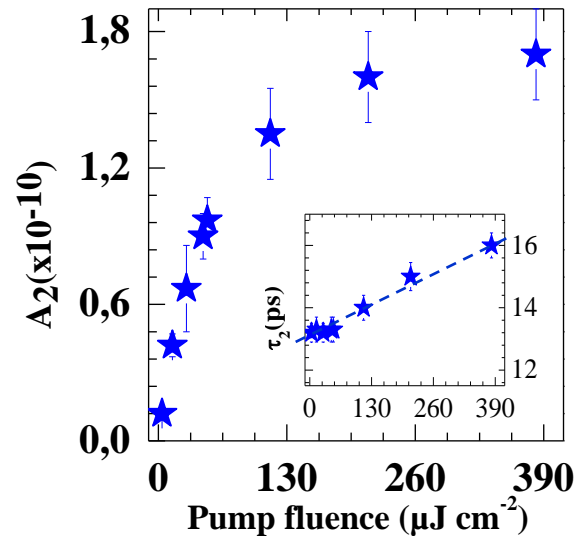


Spectroscopie pompe optique - sonde THz

Exc @ 1.55 eV



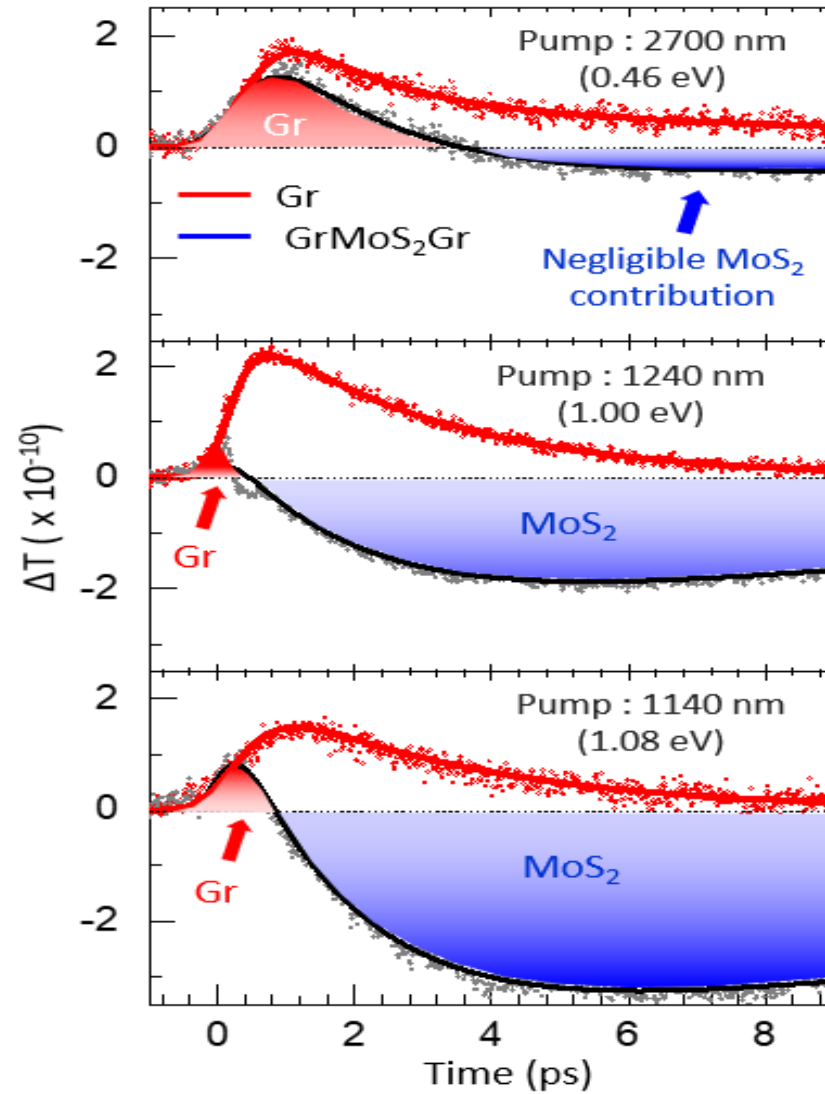
- Similar saturation intensity than graphene $\sim 130 \mu\text{J. m}^{-2}$.
- Faster relaxation $\tau_1 \sim 1.8$ ps instead of 3 ps



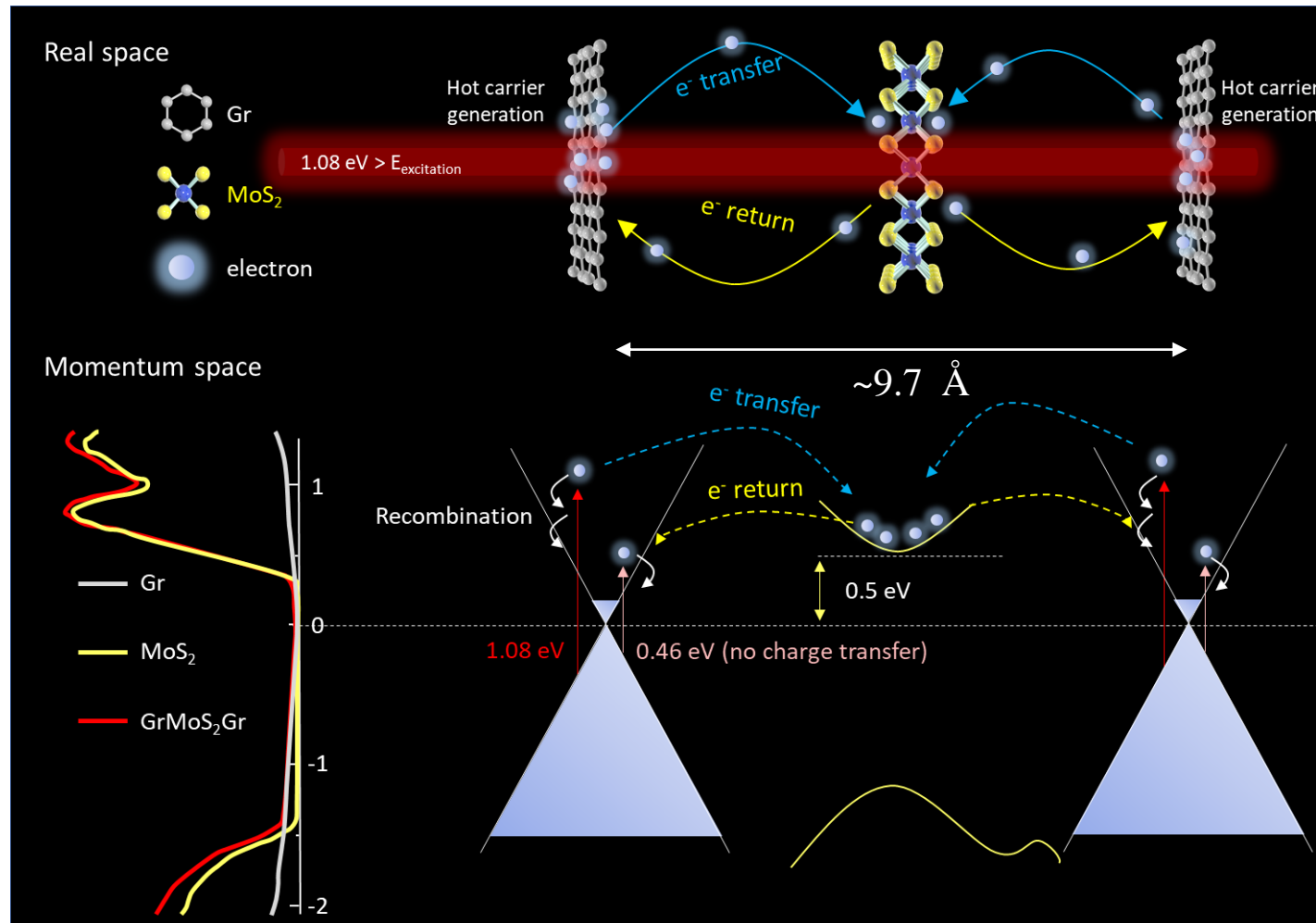
- Similar saturation intensity than graphene $\sim 130 \mu\text{J. m}^{-2}$.
- Slower relaxation $\tau_2 \sim 15$ ps instead of 12 ps than MoS₂.

Impact of the pump wavelength

Keeping a pump fluence of $\sim 50 \mu\text{J}\cdot\text{cm}^{-2}$



Mechanism in play



Conclusions and prospects

- **We have prepared a Gr/MoS₂/Gr heterostructure and we characterized it by optical absorption, Raman Spectroscopy and THz-TDS spectroscopy.**
- **Optical and Raman spectroscopy indicates that even through the weak VdW interactions A, B exciton of MoS₂ as well as Raman modes of MoS₂ and Graphene are affected.**
- **The real part of the THz conductivity of the heterostructure resembles that of graphene. The small negative part of its imaginary part stresses the conductivity is likely described by a Drude-Lorentz model.**
- **Optical-pump THz-probe experiments performed in the heterostructure below the band gap of MoS₂ indicate that carriers generated in Graphene are likely rapidly transferred towards MoS₂.**
- **We have proposed a mechanism that accounts for this phenomenon and evaluated to ~70% the number of carriers transferred from MoSe₂ to MoS₂.**
- **We have therefore demonstrated one can on demand rapidly switch, the THz conductivity of such heterostructures pumping them on a very broad spectral range.**
- **This phenomenon is not peculiar to MoS₂ and it should happen using other semiconducting TMDC**